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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





SILICON POWER MOS FET

NE5511279A

7.5 V OPERATION SILICON RF POWER LD-MOS FET FOR UHF-BAND 10 W TRANSMISSION AMPLIFIERS

DESCRIPTION

The NE5511279A is an N-channel silicon power laterally diffused MOS FET specially designed as the transmission power amplifier for 7.5 V Radio Systems. Dies are manufactured using our NEWMOS1 technology and housed in a surface mount package. This device can deliver 40.0 dBm output power with 48% power added efficiency at 900 MHz under the 7.5 V supply voltage.

FEATURES

- High output power : $P_{out} = 40.0$ dBm TYP. ($f = 900$ MHz, $V_{DS} = 7.5$ V, $P_{in} = 27$ dBm, $I_{Dset} = 400$ mA)
: $P_{out} = 40.5$ dBm TYP. ($f = 460$ MHz, $V_{DS} = 7.5$ V, $P_{in} = 25$ dBm, $I_{Dset} = 400$ mA)
- High power added efficiency : $\eta_{add} = 48\%$ TYP. ($f = 900$ MHz, $V_{DS} = 7.5$ V, $P_{in} = 27$ dBm, $I_{Dset} = 400$ mA)
: $\eta_{add} = 50\%$ TYP. ($f = 460$ MHz, $V_{DS} = 7.5$ V, $P_{in} = 25$ dBm, $I_{Dset} = 400$ mA)
- High linear gain : $G_L = 15.0$ dB TYP. ($f = 900$ MHz, $V_{DS} = 7.5$ V, $P_{in} = 5$ dBm, $I_{Dset} = 400$ mA)
: $G_L = 18.5$ dB TYP. ($f = 460$ MHz, $V_{DS} = 7.5$ V, $P_{in} = 5$ dBm, $I_{Dset} = 400$ mA)
- Surface mount package : $5.7 \times 5.7 \times 1.1$ mm MAX.
- Single supply : $V_{DS} = 2.8$ to 8.0 V

APPLICATIONS

- 460 MHz Radio Systems
- 900 MHz Radio Systems

ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
NE5511279A-T1	79A	W3	• 12 mm wide embossed taping • Gate pin face the perforation side of the tape • Qty 1 kpcs/reel
NE5511279A-T1A			• 12 mm wide embossed taping • Gate pin face the perforation side of the tape • Qty 5 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE5511279A-A

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C)

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V _{DS} ^{Note}	20	V
Gate to Source Voltage	V _{GS}	6.0	V
Drain Current	I _D	3.0	A
Total Power Dissipation	P _{tot}	20	W
Channel Temperature	T _{ch}	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

Note V_{DS} will be used under 12 V on RF operation.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V _{DS}		-	7.5	8.0	V
Gate to Source Voltage	V _{GS}		0	2.0	3.0	V
Drain Current	I _D	Duty Cycle ≤ 50%, T _{on} ≤ 1 s	-	2.5	3.0	A
Input Power	P _{in}	f = 900 MHz, V _{DS} = 7.5 V	-	27	30	dBm

ELECTRICAL CHARACTERISTICS

(T_A = +25°C, unless otherwise specified, using our standard test fixture)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I _{gss}	V _{GS} = 6.0 V	–	–	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	I _{dss}	V _{DS} = 8.5 V	–	–	100	nA
Gate Threshold Voltage	V _{th}	V _{DS} = 4.8 V, I _{DS} = 1.5 mA	1.0	1.5	2.0	V
Thermal Resistance	R _{th}	Channel to Case	–	5	–	°C/W
Transconductance	g _m	V _{DS} = 3.5 V, I _{DS} = 900 mA	–	2.3	–	S
Drain to Source Breakdown Voltage	BV _{DSS}	I _{DSS} = 15 μA	20	24	–	V
Output Power	P _{out}	f = 900 MHz, V _{DS} = 7.5 V,	38.5	40.0	–	dBm
Drain Current	I _D	P _{in} = 27 dBm,	–	2.5	–	A
Power Added Efficiency	η _{add}	I _{Dset} = 400 mA (RF OFF)	42	48	–	%
Linear Gain	G _L ^{Note}		–	15.0	–	dB
Output Power	P _{out}	f = 460 MHz, V _{DS} = 7.5 V,	–	40.5	–	dBm
Drain Current	I _D	P _{in} = 25 dBm,	–	2.75	–	A
Power Added Efficiency	η _{add}	I _{Dset} = 400 mA (RF OFF)	–	50	–	%
Linear Gain	G _L ^{Note}		–	18.5	–	dB

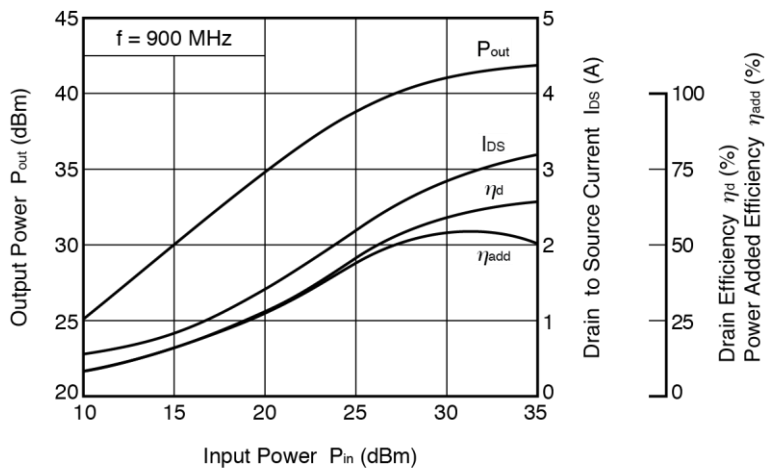
Note P_{in} = 5 dBm

DC performance is 100% testing. RF performance is testing several samples per wafer.

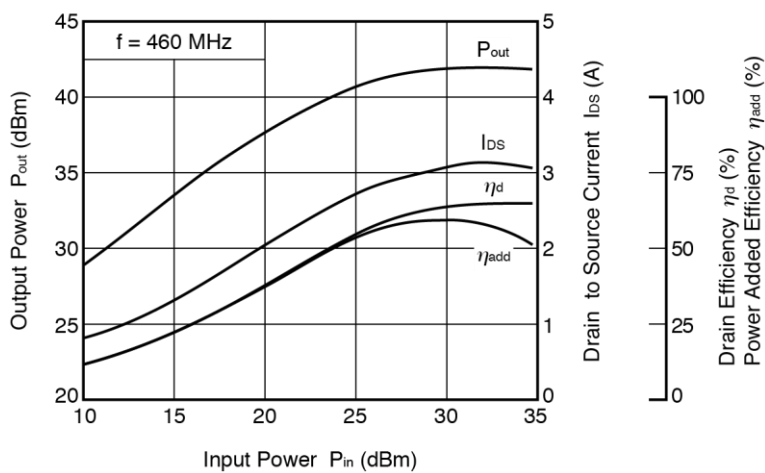
Wafer rejection criteria for standard devices is 1 reject for several samples.

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, $V_{DS} = 7.5\text{ V}$, $I_{Dset} = 400\text{ mA}$)

OUTPUT POWER, DRAIN CURRENT, η_d , η_{add} VS. INPUT POWER



OUTPUT POWER, DRAIN CURRENT, η_d , η_{add} VS. INPUT POWER



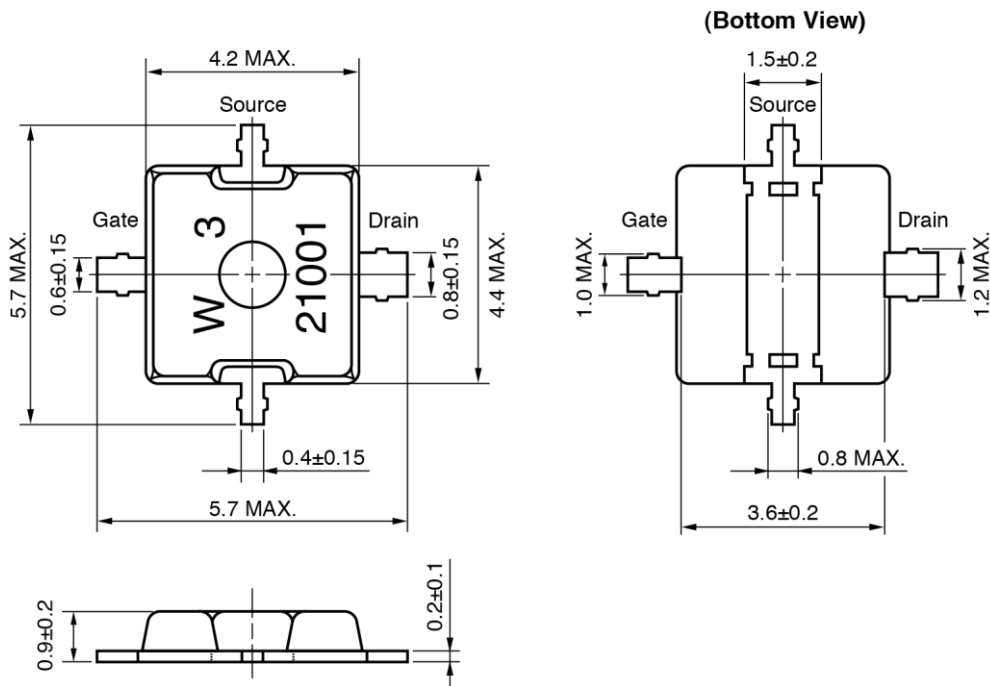
Remark The graphs indicate nominal characteristics.

S-PARAMETERS

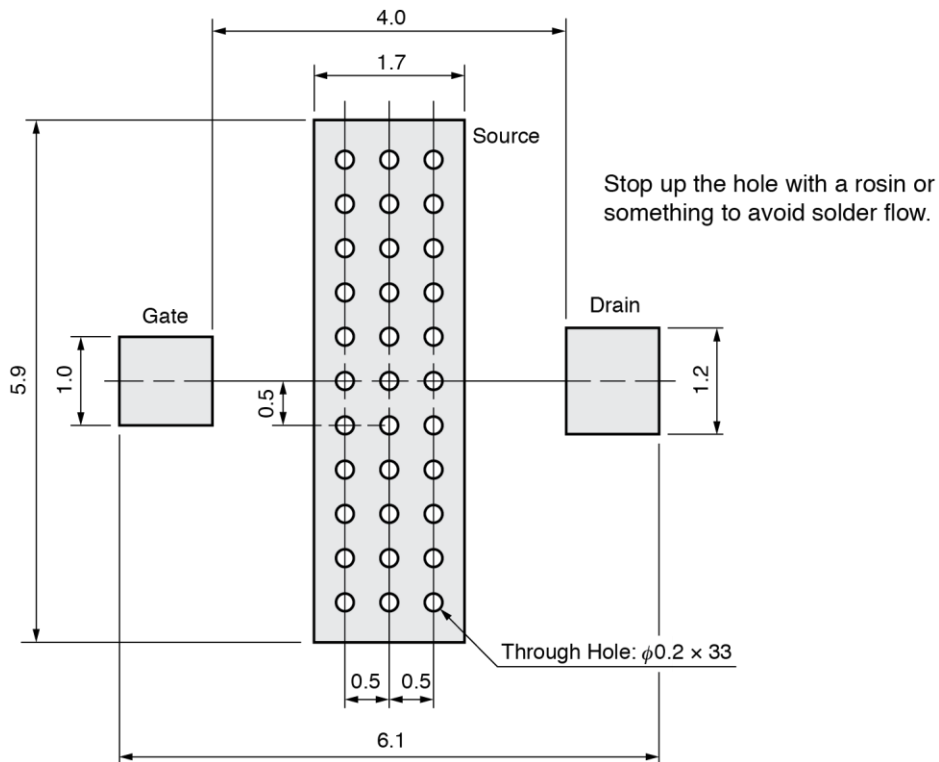
- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

PACKAGE DIMENSIONS

79A (UNIT: mm)



79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) : 215°C or below Time at temperature of 200°C or higher : 25 to 40 seconds Preheating time at 120 to 150°C : 30 to 60 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per pin of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350-P3

Caution Do not use different soldering methods together (except for partial heating).